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N-channel 250 V, 0.195 Ω , 14 A STripFET™ II Power MOSFET in DPAK, TO-220FP and TO-220 packages

Datasheet – production data

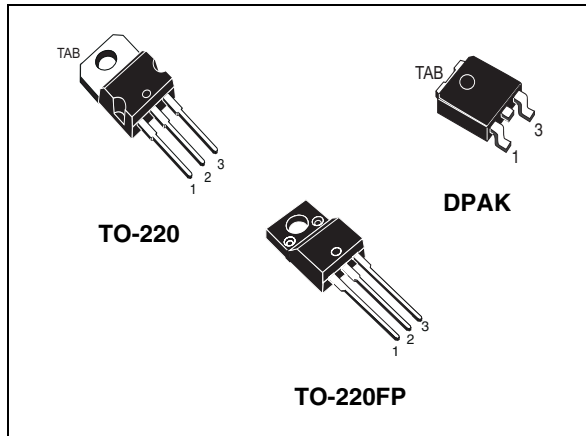
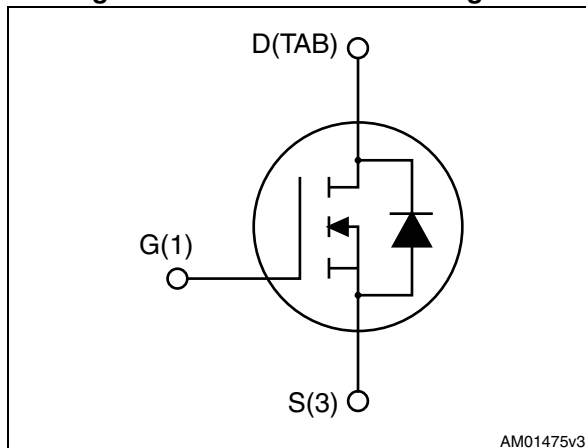


Figure 1. Internal schematic diagram



Features

| Order codes | V_{DS} | $R_{DS(on) \max}$ | I_D | P_{TOT} |
|-------------|----------|-------------------|---------------------|-----------|
| STD16NF25 | 250 V | 0.235 Ω | 14 A | 100 W |
| STF16NF25 | | | 14 A ⁽¹⁾ | 25 W |
| STP16NF25 | | | 14 A | 100 W |

1. Limited by maximum junction temperature

- Exceptional dv/dt capability
- 100% avalanche tested
- Application oriented characterization

Applications

- Switching applications

Description

These Power MOSFETs have been developed using STMicroelectronics' unique STripFET process, which is specifically designed to minimize input capacitance and gate charge. This renders the devices suitable for use as primary switch in advanced high-efficiency isolated DC-DC converters for telecom and computer applications, and applications with low gate charge driving requirements.

Table 1. Device summary

| Order codes | Marking | Package | Packaging |
|-------------|---------|----------|---------------|
| STD16NF25 | 16NF25 | DPAK | Tape and reel |
| STF16NF25 | | TO-220FP | Tube |
| STP16NF25 | | TO-220 | |

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1 Electrical ratings

Table 2. Absolute maximum ratings

| Symbol | Parameter | Value | | Unit |
|----------------------|--|----------------|--------------------|---------------------|
| | | DPAK TO-220 | TO-220FP | |
| V_{DS} | Drain-source voltage | 250 | | V |
| V_{GS} | Gate- source voltage | ± 20 | | V |
| I_D | Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$ | 14 | 14 ⁽¹⁾ | A |
| I_D | Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$ | 8.8 | 8.8 ⁽¹⁾ | A |
| $I_{DM}^{(2)}$ | Drain current (pulsed) | 56 | 56 ⁽¹⁾ | A |
| P_{TOT} | Total dissipation at $T_C = 25\text{ }^\circ\text{C}$ | 85 | 25 | W |
| | Derating factor | 0.68 | 0.2 | W/ $^\circ\text{C}$ |
| dv/dt ⁽³⁾ | Peak diode recovery voltage slope | 15 | | V/ns |
| V_{ISO} | Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; $T_C = 25\text{ }^\circ\text{C}$) | | 2500 | V |
| T_{stg} | Storage temperature | -55 to 150 | | $^\circ\text{C}$ |
| T_j | Max. operating junction temperature | | | |

1. Limited by maximum junction temperature
2. Pulse width limited by safe operating area.
3. $I_{SD} \leq 13\text{A}$, $di/dt \leq 300\text{A}/\mu\text{s}$, $V_{DD} \leq 80\% V_{(BR)DSS}$, $T_j \leq T_{JMAX}$

Table 3. Thermal data

| Symbol | Parameter | Value | | | Unit |
|----------------|---|--------|------|----------|---------------------------|
| | | TO-220 | DPAK | TO-220FP | |
| $R_{thj-case}$ | Thermal resistance junction-case max | 1.47 | | 5 | $^\circ\text{C}/\text{W}$ |
| $R_{thj-pcb}$ | Thermal resistance junction to pcb max | | 50 | | $^\circ\text{C}/\text{W}$ |
| $R_{thj-amb}$ | Thermal resistance junction-ambient max | 62.5 | | 62.5 | $^\circ\text{C}/\text{W}$ |

Table 4. Avalanche characteristics

| Symbol | Parameter | Value | Unit |
|----------|--|-------|------|
| I_{AR} | Avalanche current, repetitive or not-repetitive (pulse width limited by T_{jmax}) | 13 | A |
| E_{AS} | Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_{AR} = 13\text{ A}$, $V_{DD} = 50\text{ V}$) | 100 | mJ |

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|-----------------------------------|--|------|-------|-----------|---------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $V_{GS} = 0, I_D = 1\text{ mA}$ | 250 | | | V |
| I_{DSS} | Zero gate voltage drain current | $V_{GS} = 0, V_{DS} = 250\text{ V}$ | | | 1 | μA |
| | | $V_{GS} = 0, V_{DS} = 250\text{ V}, T_C = 125\text{ °C}$ | | | 10 | μA |
| I_{GSS} | Gate-body leakage current | $V_{DS} = 0, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 2 | 3 | 4 | V |
| $R_{DS(on)}$ | Static drain-source on-resistance | $V_{GS} = 10\text{ V}, I_D = 6.5\text{ A}$ | | 0.195 | 0.235 | Ω |

Table 6. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|----------------------------|-------------------------------|--|------|------|------|----------|
| C_{iss} | Input capacitance | $V_{DS} = 25\text{ V}, f = 1\text{ MHz}, V_{GS} = 0$ | - | 680 | - | pF |
| C_{oss} | Output capacitance | | - | 125 | - | pF |
| C_{rss} | Reverse transfer capacitance | | - | 20 | - | pF |
| $C_{oss\text{ eq.}}^{(1)}$ | Equivalent output capacitance | $V_{DS} = 0\text{ to }200\text{ V}, V_{GS} = 0$ | - | 48 | - | pF |
| R_G | Intrinsic gate resistance | $f = 1\text{ MHz}, I_D = 0$ | - | 2.1 | - | Ω |
| Q_g | Total gate charge | $V_{DD} = 200\text{ V}, I_D = 13\text{ A}, V_{GS} = 10\text{ V}$ (see Figure 19) | - | 18 | - | nC |
| Q_{gs} | Gate-source charge | | - | 3 | - | nC |
| Q_{gd} | Gate-drain charge | | - | 8 | - | nC |

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|--------------|---------------------|--|------|------|------|------|
| $t_{d(on)}$ | Turn-on delay time | $V_{DD} = 125\text{ V}$, $I_D = 6.5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 18) | - | 9 | - | ns |
| t_r | Rise time | | - | 17 | - | ns |
| $t_{d(off)}$ | Turn-off delay time | | - | 35 | - | ns |
| t_f | Fall time | | - | 17 | - | ns |

Table 8. Source drain diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------|-------------------------------|---|------|------|------|------|
| I_{SD} | Source-drain current | | - | - | 14 | A |
| $I_{SDM}^{(1)}$ | Source-drain current (pulsed) | | - | - | 56 | A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD} = 13\text{ A}$, $V_{GS} = 0$ | - | - | 1.6 | V |
| t_{rr} | Reverse recovery time | $I_{SD} = 13\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 20) | - | 133 | | ns |
| Q_{rr} | Reverse recovery charge | | - | 651 | | nC |
| I_{RRM} | Reverse recovery current | | - | 10 | | A |
| t_{rr} | Reverse recovery time | $I_{SD} = 13\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 20) | - | 157 | | ns |
| Q_{rr} | Reverse recovery charge | | - | 895 | | nC |
| I_{RRM} | Reverse recovery current | | - | 11 | | A |

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220

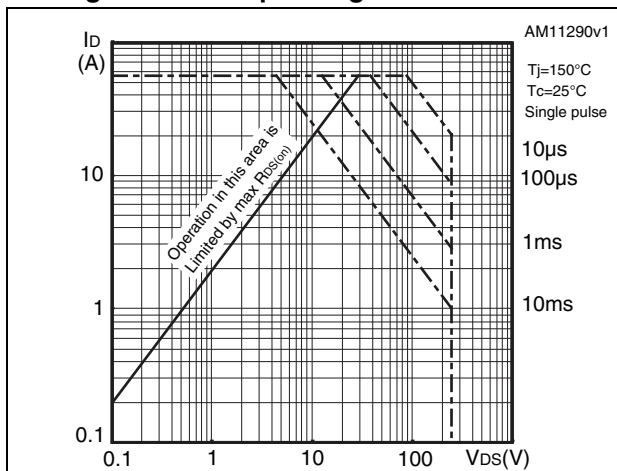


Figure 3. Thermal impedance for TO-220

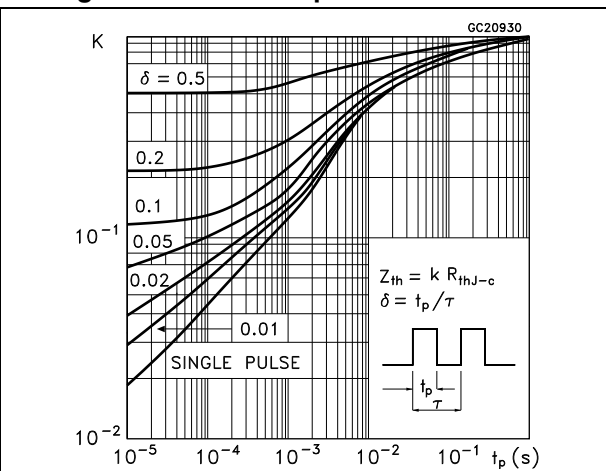


Figure 4. Safe operating area for TO-220FP

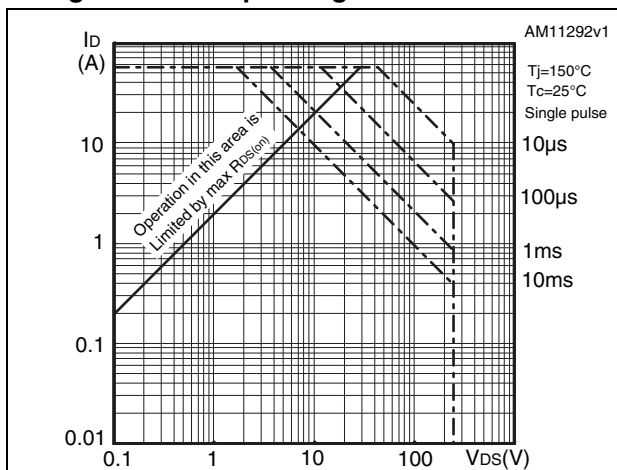


Figure 5. Thermal impedance for TO-220FP

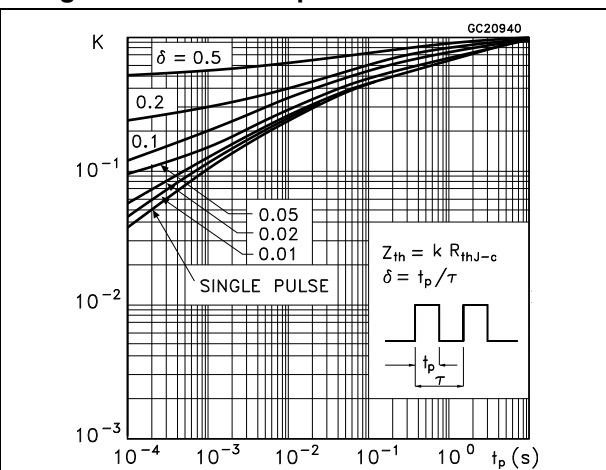


Figure 6. Safe operating area for DPAK

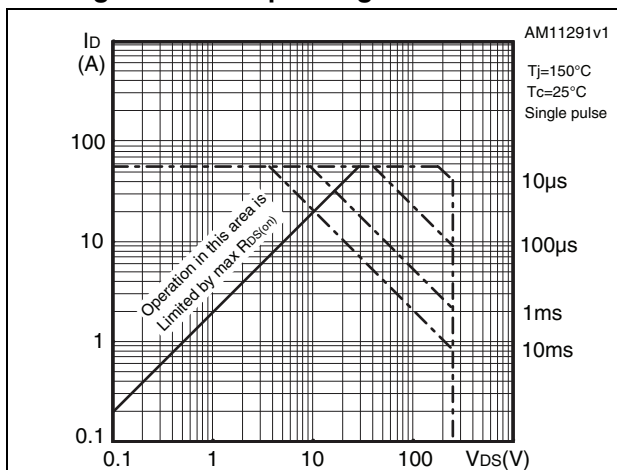


Figure 7. Thermal impedance for DPAK

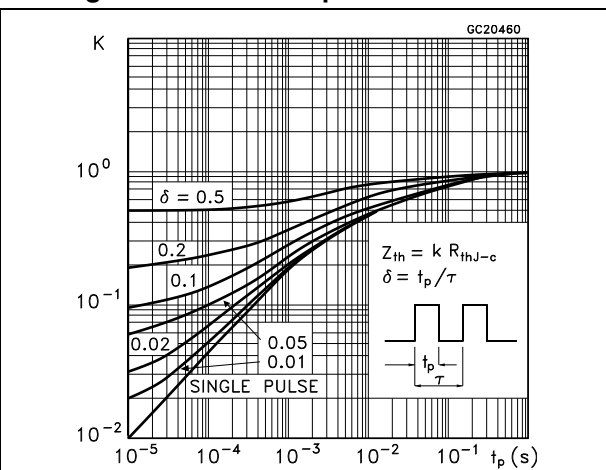


Figure 8. Output characteristics

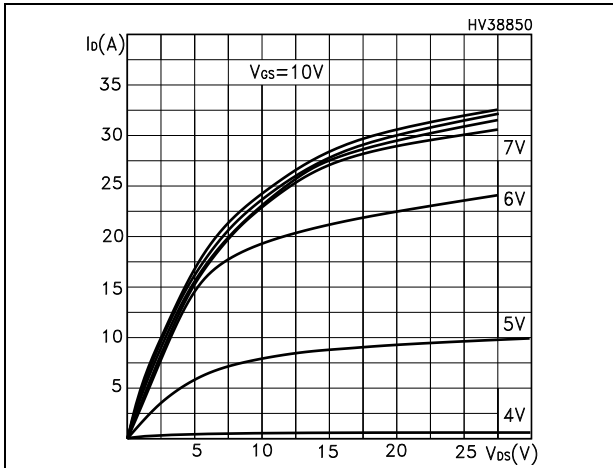


Figure 9. Transfer characteristics

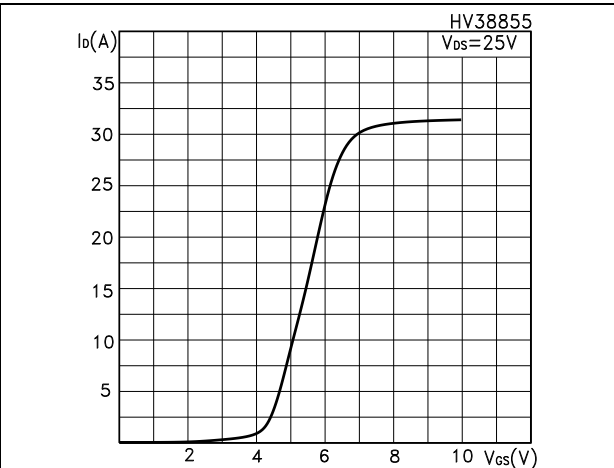


Figure 10. Normalized BV_{DSS} vs temperature

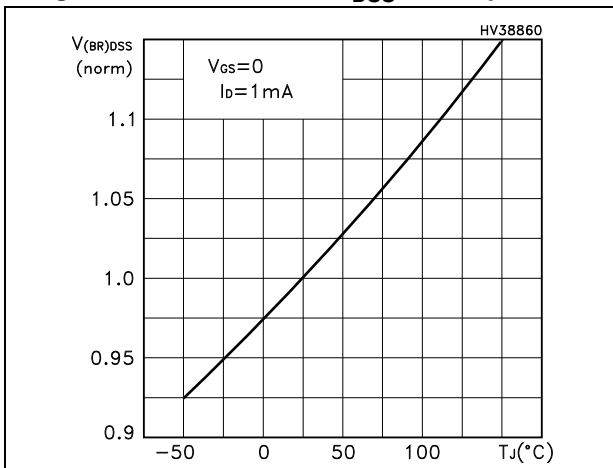


Figure 11. Static-drain source on-resistance

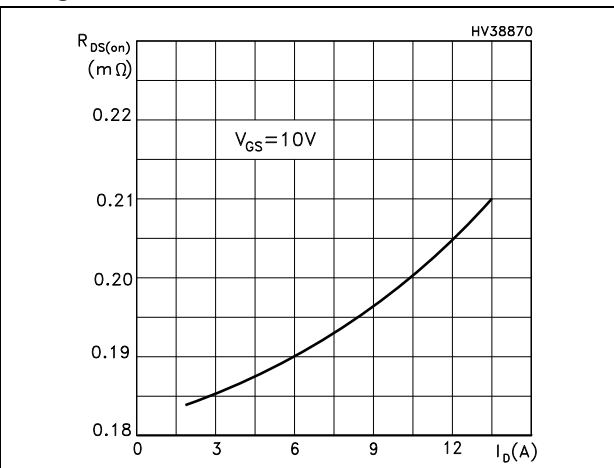


Figure 12. Gate charge vs gate-source voltage

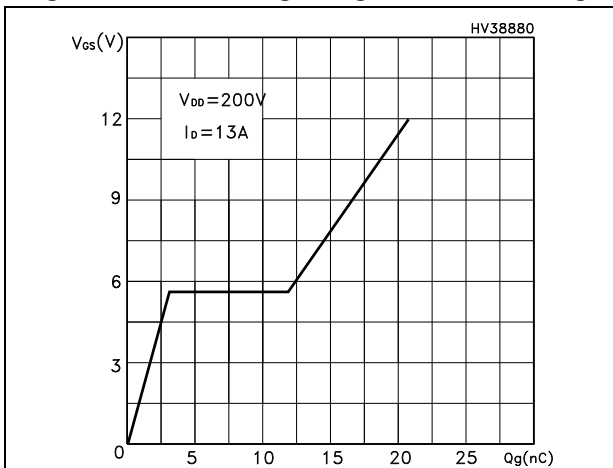


Figure 13. Capacitance variations

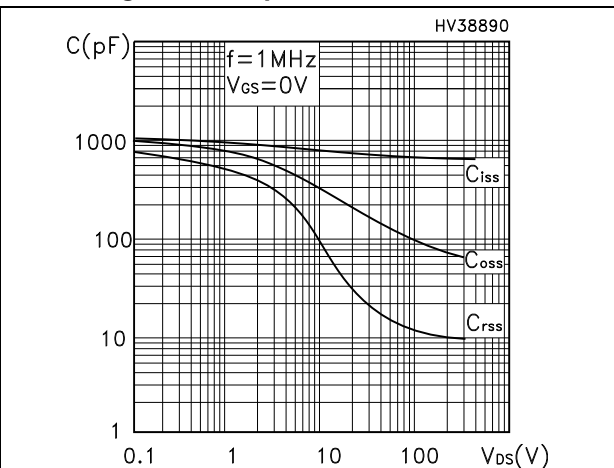


Figure 14. Normalized gate threshold voltage vs temperature

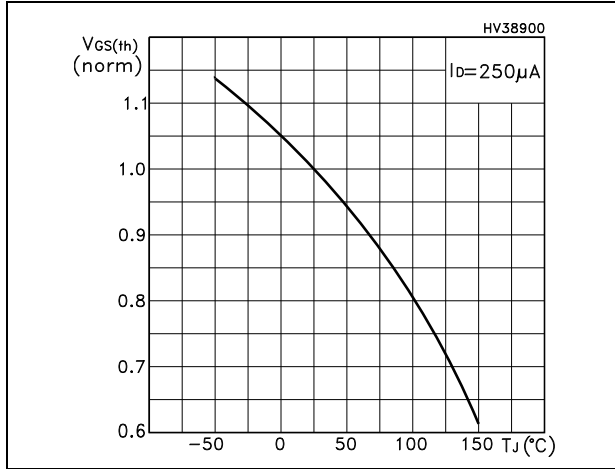


Figure 15. Normalized on-resistance vs temperature

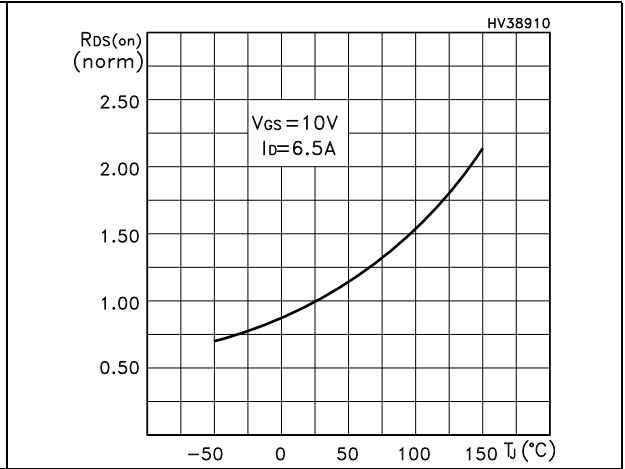


Figure 16. Source-drain diode forward characteristics

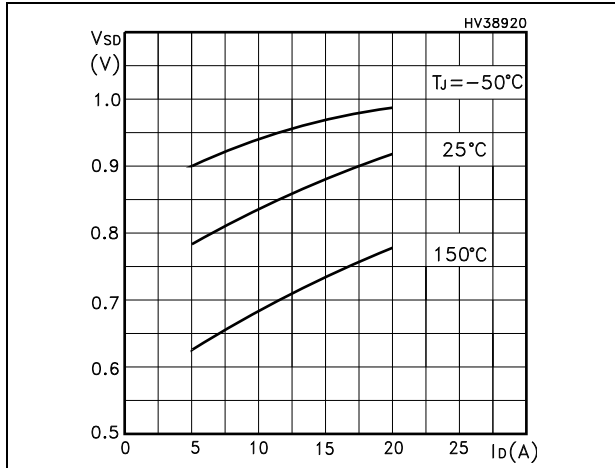
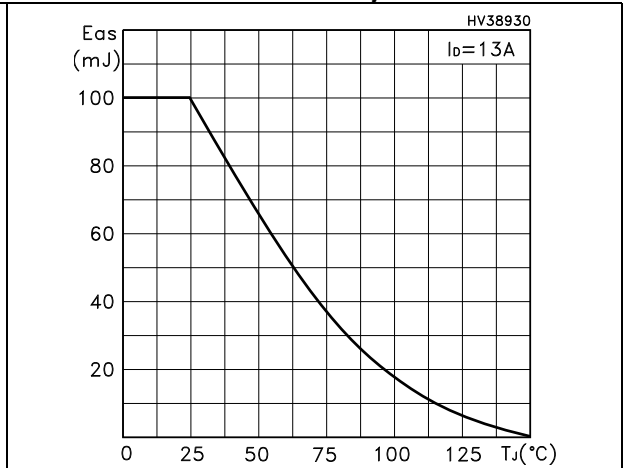


Figure 17. Maximum avalanche energy vs starting Tj



3 Test circuit

Figure 18. Switching times test circuit for resistive load

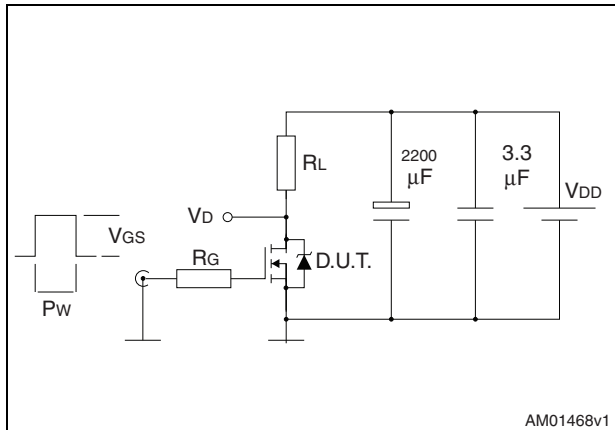


Figure 19. Gate charge test circuit

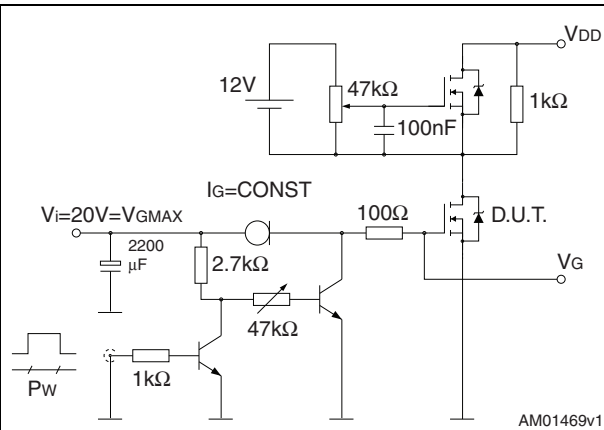


Figure 20. Test circuit for inductive load switching and diode recovery times

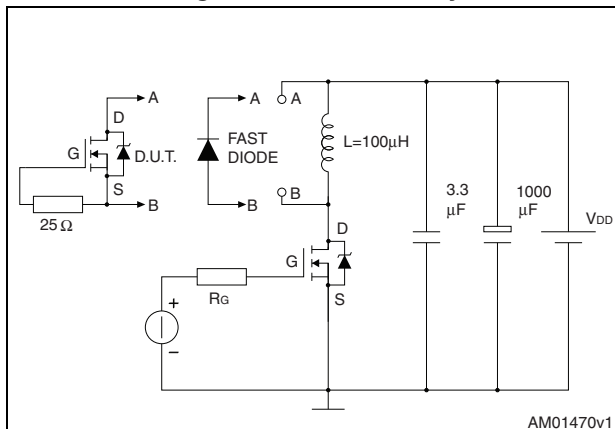


Figure 21. Unclamped inductive load test circuit

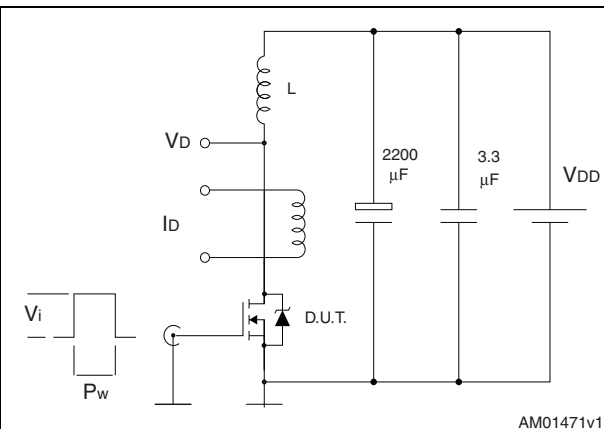


Figure 22. Unclamped inductive waveform

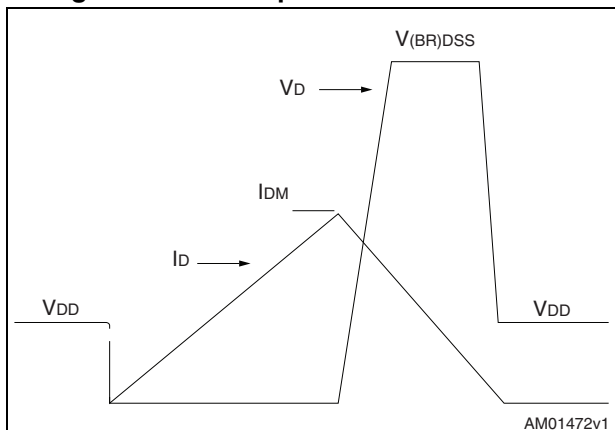
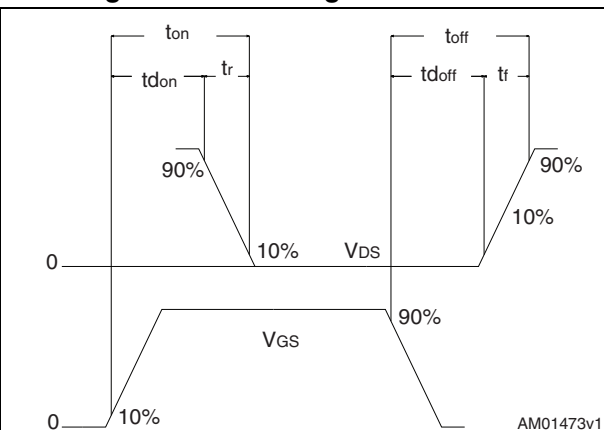


Figure 23. Switching time waveform



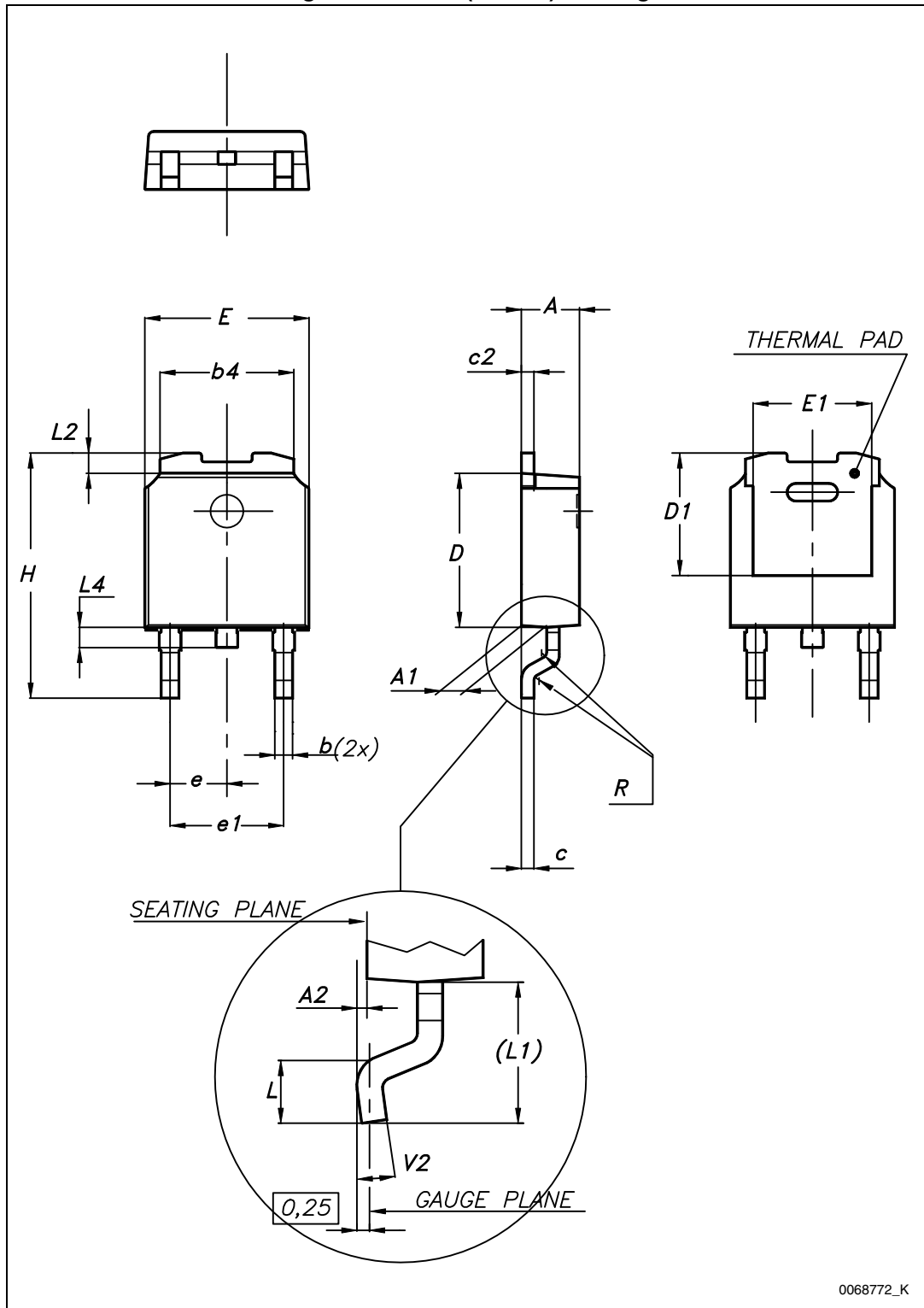
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 9. DPAK (TO-252) mechanical data

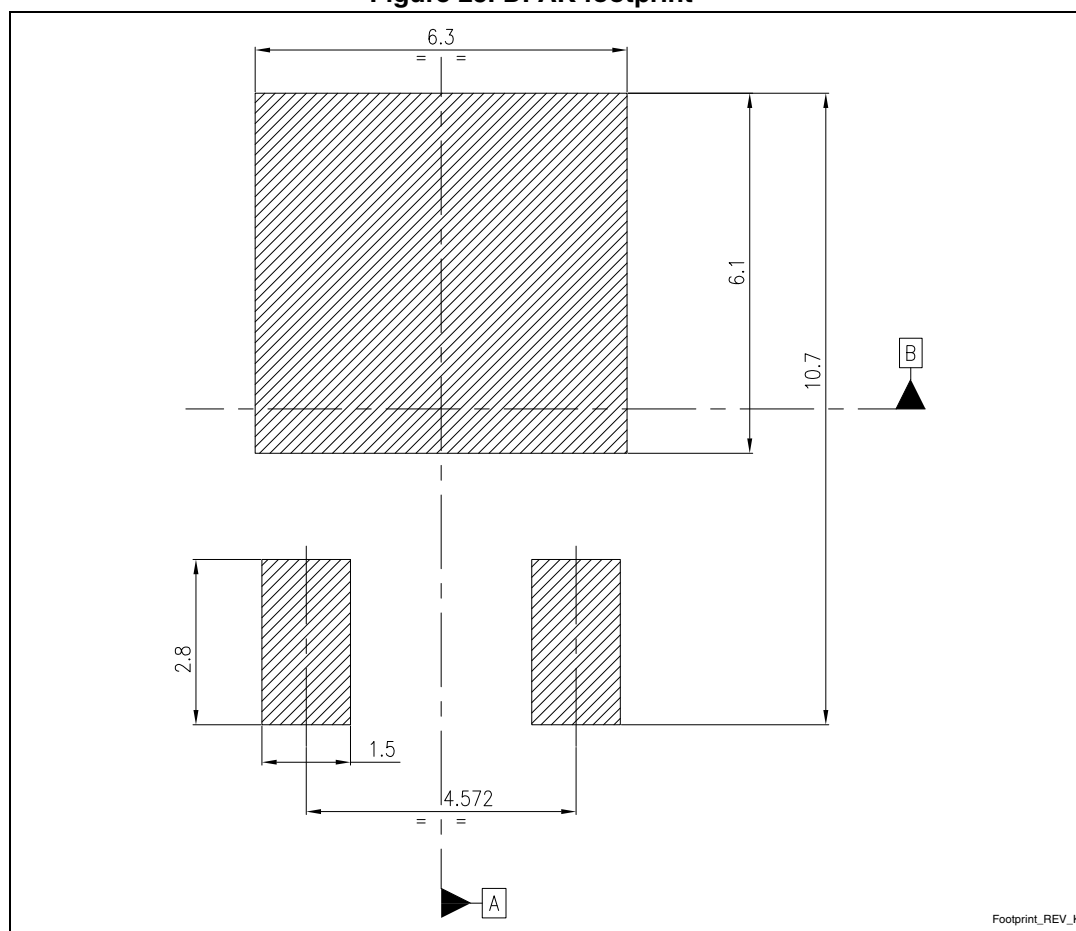
| Dim. | mm | | |
|------|------|------|-------|
| | Min. | Typ. | Max. |
| A | 2.20 | | 2.40 |
| A1 | 0.90 | | 1.10 |
| A2 | 0.03 | | 0.23 |
| b | 0.64 | | 0.90 |
| b4 | 5.20 | | 5.40 |
| c | 0.45 | | 0.60 |
| c2 | 0.48 | | 0.60 |
| D | 6.00 | | 6.20 |
| D1 | | 5.10 | |
| E | 6.40 | | 6.60 |
| E1 | | 4.70 | |
| e | | 2.28 | |
| e1 | 4.40 | | 4.60 |
| H | 9.35 | | 10.10 |
| L | 1.00 | | 1.50 |
| (L1) | | 2.80 | |
| L2 | | 0.80 | |
| L4 | 0.60 | | 1.00 |
| R | | 0.20 | |
| V2 | 0° | | 8° |

Figure 24. DPAK (TO-252) drawing



0068772_K

Figure 25. DPAK footprint (a)



a. All dimensions are in millimeters

Table 10. TO-220FP mechanical data

| Dim. | mm | | |
|------|------|------|------|
| | Min. | Typ. | Max. |
| A | 4.4 | | 4.6 |
| B | 2.5 | | 2.7 |
| D | 2.5 | | 2.75 |
| E | 0.45 | | 0.7 |
| F | 0.75 | | 1 |
| F1 | 1.15 | | 1.70 |
| F2 | 1.15 | | 1.70 |
| G | 4.95 | | 5.2 |
| G1 | 2.4 | | 2.7 |
| H | 10 | | 10.4 |
| L2 | | 16 | |
| L3 | 28.6 | | 30.6 |
| L4 | 9.8 | | 10.6 |
| L5 | 2.9 | | 3.6 |
| L6 | 15.9 | | 16.4 |
| L7 | 9 | | 9.3 |
| Dia | 3 | | 3.2 |

Figure 26. TO-220FP drawing

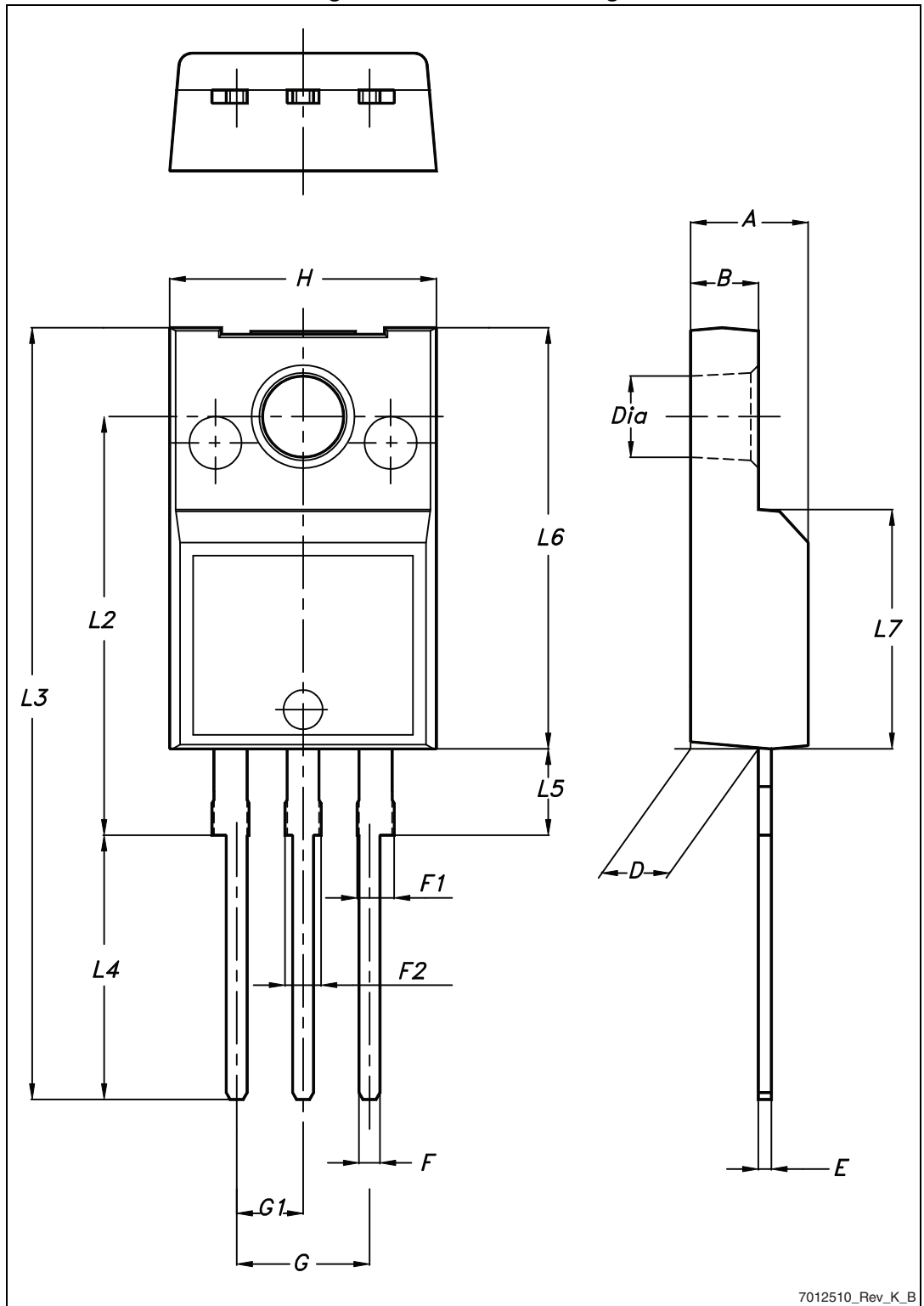
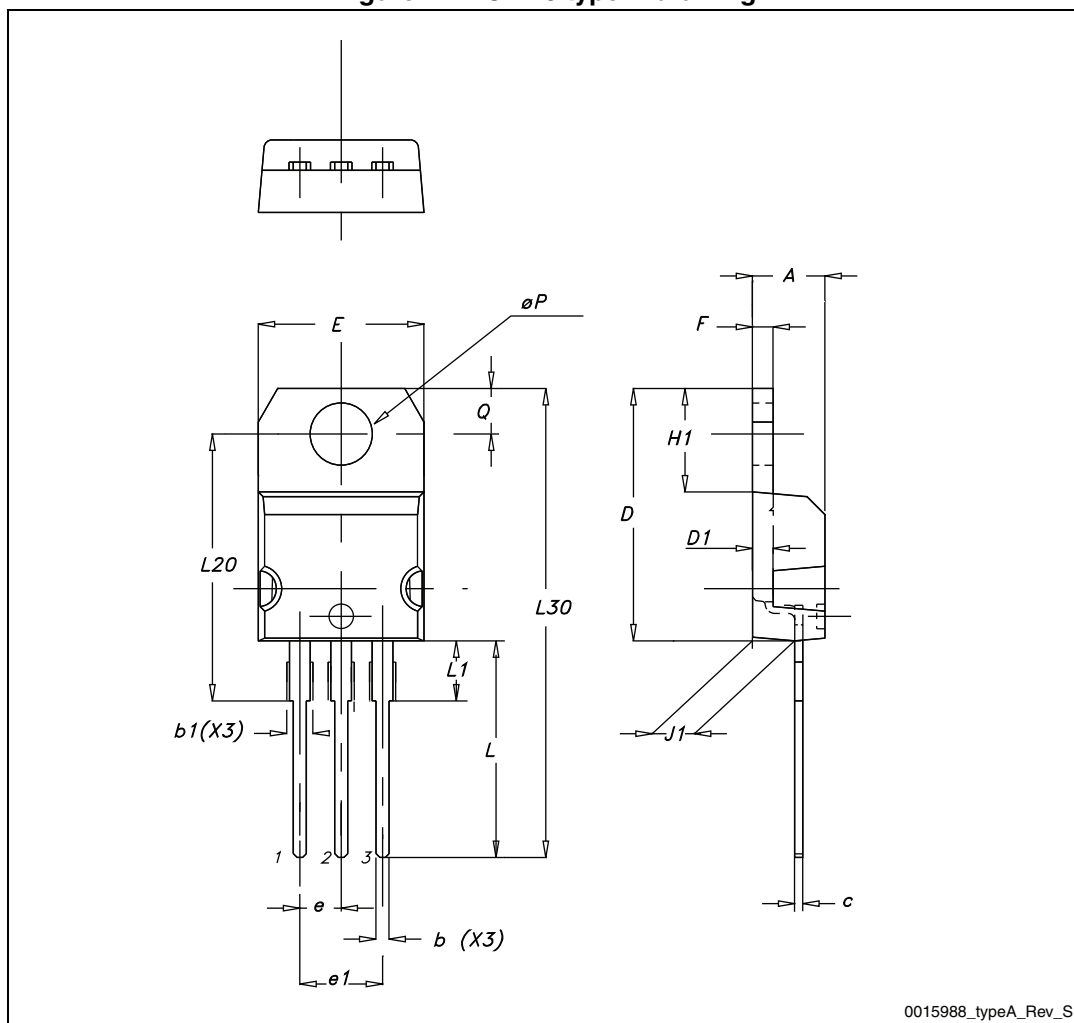


Table 11. TO-220 type A mechanical data

| Dim. | mm | | |
|------|-------|-------|-------|
| | Min. | Typ. | Max. |
| A | 4.40 | | 4.60 |
| b | 0.61 | | 0.88 |
| b1 | 1.14 | | 1.70 |
| c | 0.48 | | 0.70 |
| D | 15.25 | | 15.75 |
| D1 | | 1.27 | |
| E | 10 | | 10.40 |
| e | 2.40 | | 2.70 |
| e1 | 4.95 | | 5.15 |
| F | 1.23 | | 1.32 |
| H1 | 6.20 | | 6.60 |
| J1 | 2.40 | | 2.72 |
| L | 13 | | 14 |
| L1 | 3.50 | | 3.93 |
| L20 | | 16.40 | |
| L30 | | 28.90 | |
| ØP | 3.75 | | 3.85 |
| Q | 2.65 | | 2.95 |

Figure 27. TO-220 type A drawing



0015988_typeA_Rev_S

5 Packaging mechanical data

Table 12. DPAK (TO-252) tape and reel mechanical data

| Tape | | | Reel | | |
|------|------|------|-----------|------|------|
| Dim. | mm | | Dim. | mm | |
| | Min. | Max. | | Min. | Max. |
| A0 | 6.8 | 7 | A | | 330 |
| B0 | 10.4 | 10.6 | B | 1.5 | |
| B1 | | 12.1 | C | 12.8 | 13.2 |
| D | 1.5 | 1.6 | D | 20.2 | |
| D1 | 1.5 | | G | 16.4 | 18.4 |
| E | 1.65 | 1.85 | N | 50 | |
| F | 7.4 | 7.6 | T | | 22.4 |
| K0 | 2.55 | 2.75 | | | |
| P0 | 3.9 | 4.1 | Base qty. | | 2500 |
| P1 | 7.9 | 8.1 | Bulk qty. | | 2500 |
| P2 | 1.9 | 2.1 | | | |
| R | 40 | | | | |
| T | 0.25 | 0.35 | | | |
| W | 15.7 | 16.3 | | | |

Figure 28. Tape for DPAK (TO-252)

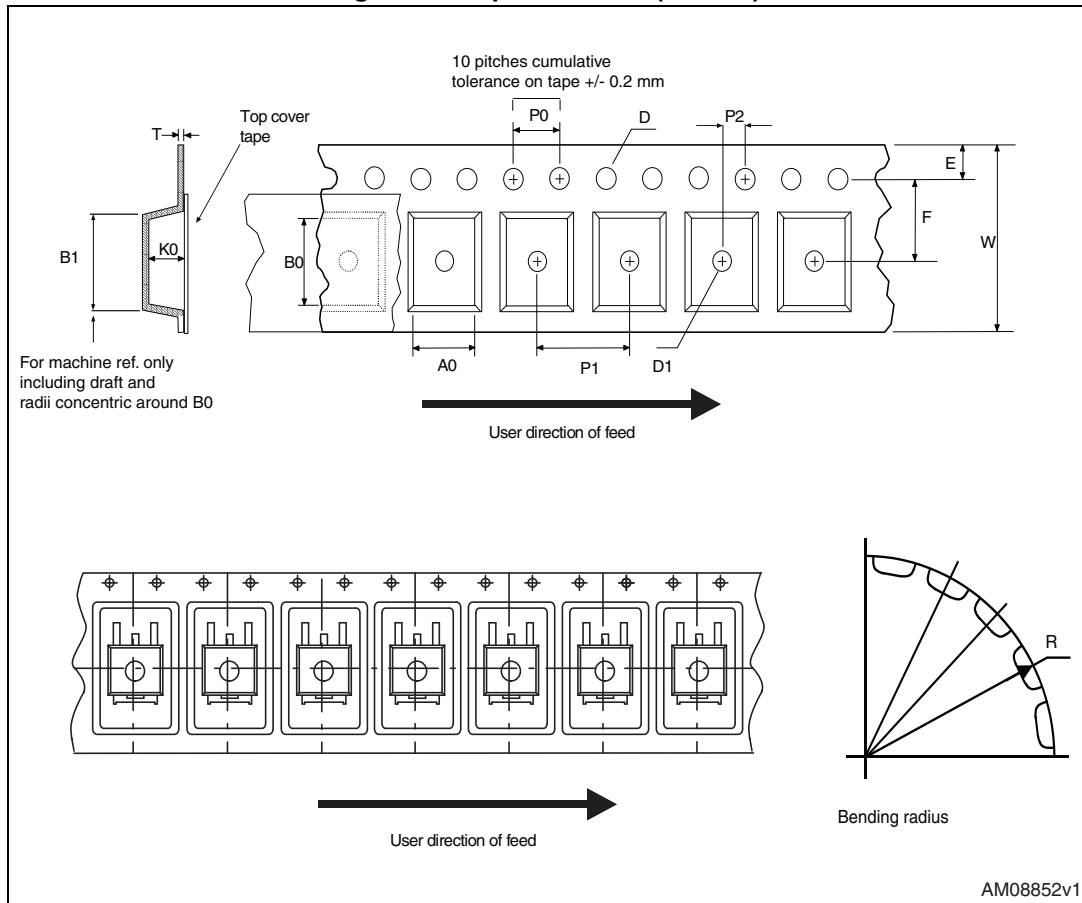
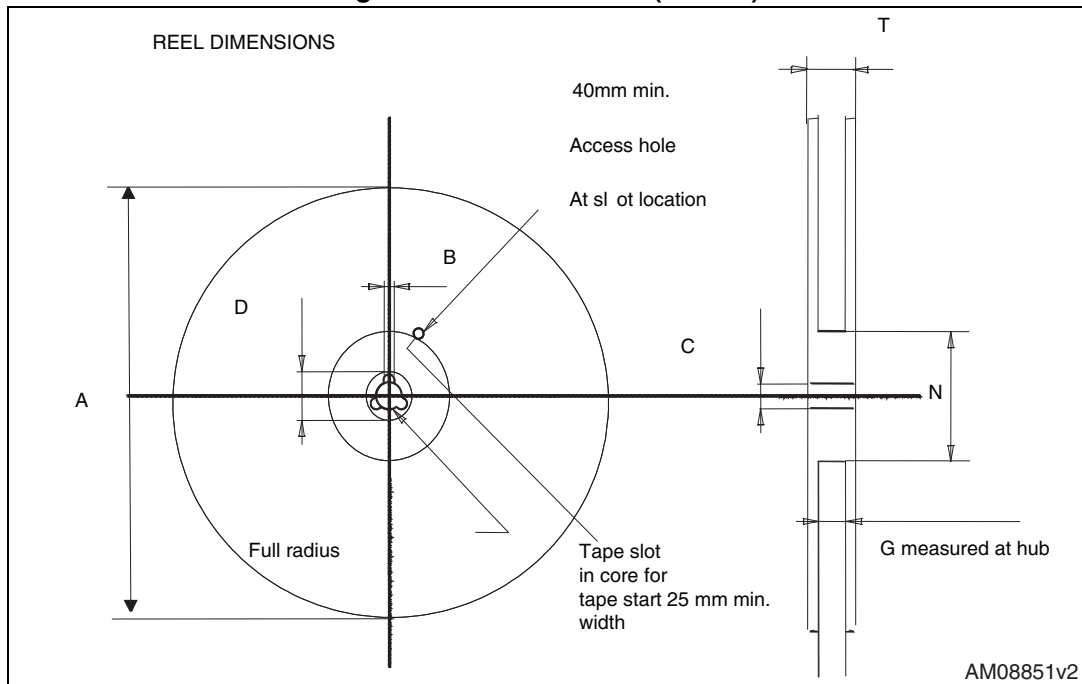


Figure 29. Reel for DPAK (TO-252)



6 Revision history

Table 13. Document revision history

| Date | Revision | Changes |
|-------------|----------|--|
| 12-Oct-2007 | 1 | Initial release. |
| 13-Nov-2007 | 2 | Modified: <i>Figure 13: Capacitance variations</i> . |
| 29-Mar-2012 | 3 | <p><i>Figure 2: Safe operating area for TO-220</i>, <i>Figure 4: Safe operating area for TO-220FP</i> and <i>Figure 6: Safe operating area for DPAK</i> have been updated.</p> <p><i>Section 4: Package mechanical data</i> and <i>Section 5: Packaging mechanical data</i> have been updated.</p> <p>Minor text changes</p> |
| 06-Mar-2013 | 4 | <ul style="list-style-type: none"> – Modified: P_{TOT}, derating factor values, <i>note 1</i> on <i>Table 2</i>, $R_{thj-case}$, $R_{thj-amb}$ only for TO-220 and DPAK – Updated: <i>Section 4: Package mechanical data</i> – Minor text changes |

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